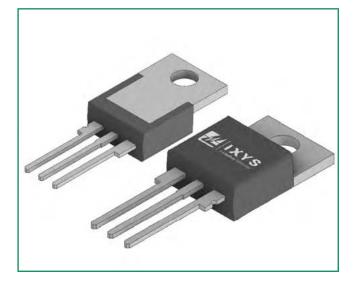
## Thyristors Datasheet

# MAC16HCDG, MAC16HCMG, MAC16HCNG TRIAC - 400V - 800V

# RoHS 🔗



## Description

Designed primarily for full-wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full-wave, silicon gate-controlled devices are needed.

## Features

- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS at 80°C
- Industry Standard TO-220 Package for Ease of Design
  Glass Passivated Junctions

- 150 Amperes

High Surge Current Capability

- Glass Passivated Junctions for Reliability and Uniformity
- These Devices are Pb–Free and are RoHS Compliant

## **Additional Information**





Resources

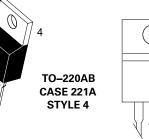
Accessories



Samples

### **Functional Diagram**

Pin Out



### Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) MAC16HCD   (- 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MAC16HCM   MAC16HCN MAC16HCN		V <sub>drm</sub> , V <sub>rrm</sub>	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 80^{\circ}$ C)		I <sub>T (RMS)</sub>	16	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_c$ = 125°C)		I <sub>TSM</sub>	150	А
Circuit Fusing Consideration (t = 8.3 ms)		l²t	93	A <sup>2</sup> sec
Peak Gate Power (T <sub>c</sub> = 80°C, Pulse Width $\leq$ 1.0 µs)	P <sub>gM</sub>	20	W	
Average Gate Power (t = 8.3 ms, $T_c = 80^{\circ}$ C)		P <sub>G(AV)</sub>	0.5	W
Operating Junction Temperature Range		T,	-40 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V<sub>DEM</sub> and V<sub>SEM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

#### **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		TL	260	°C

#### Electrical Characteristics - OFF (TJ = 25°C unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Мах	Unit
Peak Repetitive Blocking Current	T_ = 25°C	I <sub>DRM</sub> ,	-	-	0.01	~^
$(V_{D} = V_{DRM} = V_{RRM}; \text{ Gate Open})$	T_ = 125°C	I	-	-	2.0	mA

#### Electrical Characteristics - ON (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic			Min	Тур	Мах	Unit
Peak On–State Voltage (Note 2) ( $I_{TM} = \pm 21$ A Peak)		V <sub>TM</sub>	_	-	1.6	V
Gate Trigger Current	MT2(+), G(+)		10	16	50	
(Continuous dc)	MT2(+), G(-)	I <sub>gt</sub>	10	18	50	mA
$(V_{\rm D} = 12 \text{ V}, \text{ R}_{\rm L} = 100 \Omega)$ MT2	MT2(-), G(-)		10	22	50	
Gate Trigger Voltage	MT2(+), G(+)		0.5	0.8	1.5	
(Continuous dc)	MT2(+), G(-)	$V_{GT}$	0.5	0.73	1.5	V
$(V_{\rm D} = 12 \text{ V}, \text{ R}_{\rm L} = 100 \Omega)$	MT2(-), G(-)		0.5	0.82	1.5	
	MT2(+), G(+)		_	33	60	
Latching Current ( $V_p = 24 \text{ V}, I_c = 50 \text{ mA}$ )	MT2(+), G(-)	$V_{GD}$	_	36	80	V
$(v_{\rm D} - 2 + v_{\rm r})_{\rm G} = 300$ mm y	MT2(-), G(-)		_	33	50	
Holding Current ( $V_{D} = 12 V_{dc'}$ Gate Open, Initiating Current = ±150 mA))		I <sub>H</sub>	_	20	50	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.

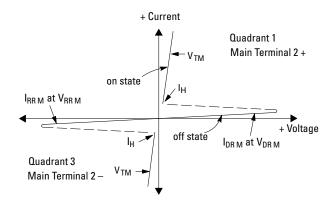


## **Dynamic Characteristics**

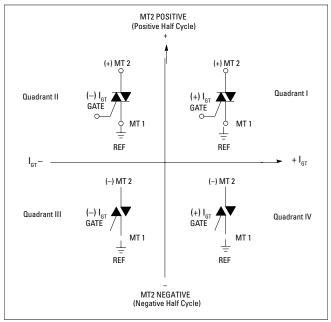
Characteristic	Symbol	Min	Тур	Мах	Unit
Rate of Change of Commutating Current ( $V_D = 400 \text{ V}$ , $I_{TM} = 6.0 \text{ A}$ , Commutating dV/dt = 20 V/µs, Gate Open, $T_J = 125^{\circ}$ C, f = 250 Hz, C <sub>1</sub> = 10 µF, L <sub>1</sub> = 40 mH, with Snubber)	(di/dt)c	15.0	-	-	A/ms
Critical Rate of Rise of Off-State Voltage ( $V_p$ = Rated $V_{DRM}$ , Exponential Waveform, Gate Open, $T_1$ = 125°C)	dv/dt	750	-	_	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 $\mu$ sec; diG/dt = 200 mA/ $\mu$ sec; f = 60 Hz	di/dt	-	-	10	A/µs

## **Voltage Current Characteristic of SCR**

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current



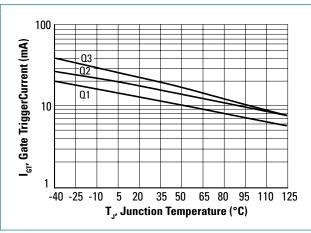
### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

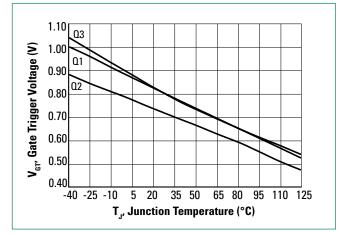
With in-phase signals (using standard AC lines) quadrants I and III are used.



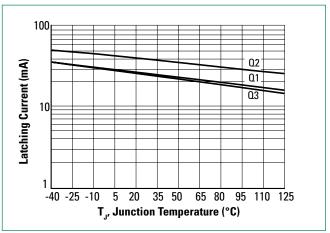


### Figure 1. Typical Gate Trigger Current vs Junction Temperature

Figure 2. Typical Gate Trigger Voltage vs Junction Temperature



### Figure 4. Typical Latching Current vs Junction Temperature





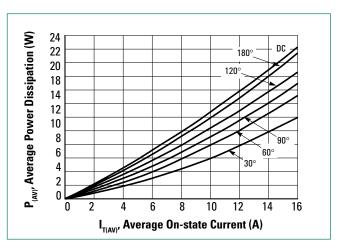


Figure 3. Typical Holding Current vs Junction Temperature

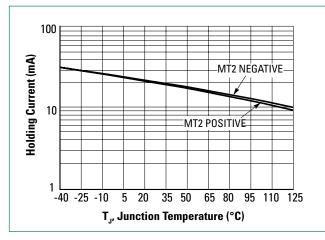
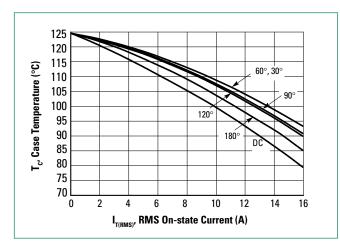
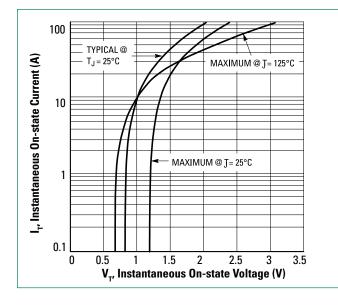
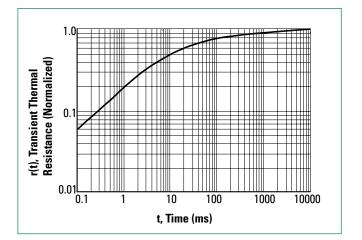


Figure 5. Typical RMS Current Derating





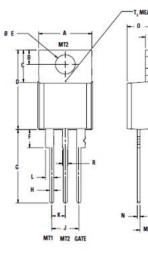
### Figure 7. Typical On-State Characteristics

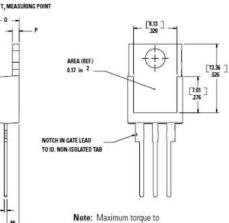


#### Figure 8. Typical Thermal Response

### Thyristors Datasheet

### Dimensions

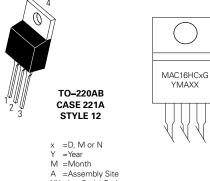




Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

	Millimeters		Inc	hes	
Dim	Min	Мах	Min	Мах	
Α	0.380	0.420	9.65	10.67	
В	0.105	0.115	2.67	2.92	
С	0.230	0.250	5.84	6.35	
D	0.590	0.620	14.99	15.75	
E	0.142	0.147	3.61	3.73	
F	0.110	0.130	2.79	3.30	
G	0.540	0.575	13.72	14.61	
Н	0.025	0.035	0.64	0.89	
J	0.195	0.205	4.95	5.21	
К	0.095	0.105	2.41	2.67	
L	0.060	0.075	1.52	1.91	
М	0.085	0.095	2.16	2.41	
Ν	0.018	0.024	0.46	0.61	
0	0.178	0.188	4.52	4.78	
Р	0.045	0.060	1.14	1.52	
R	0.038	0.048	0.97	1.22	

#### **Part Marking System**



XX =Lot Serial Code G =Pb-Free Package

Pin Assignment					
1	Main Terminal 1				
2	Main Terminal 2				
3	Gate				
4	Main Terminal 2				

### **Ordering Information**

Device	Package	Shipping	
MAC16HCDG	70.000		
MAC16HCMG	TO-220 (Pb-Free)	1000 Units/ Box	
MAC16HCNG	(151100)		

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